



ELECTRONICS, INC.
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NTE2339 Silicon NPN Transistor High Voltage, High Speed Switch TO-220 Full Pack

Features:

- High Breakdown Voltage, High Reliability
- Fast Switching Speed
- Wide Safe Operating Area

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	1100V
Collector-Emitter Voltage, V_{CEO}	800V
Emitter-Base Voltage, V_{EBO}	7V
Collector Current, I_C	
Continuous	3A
Peak (Note 1)	10A
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	30W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

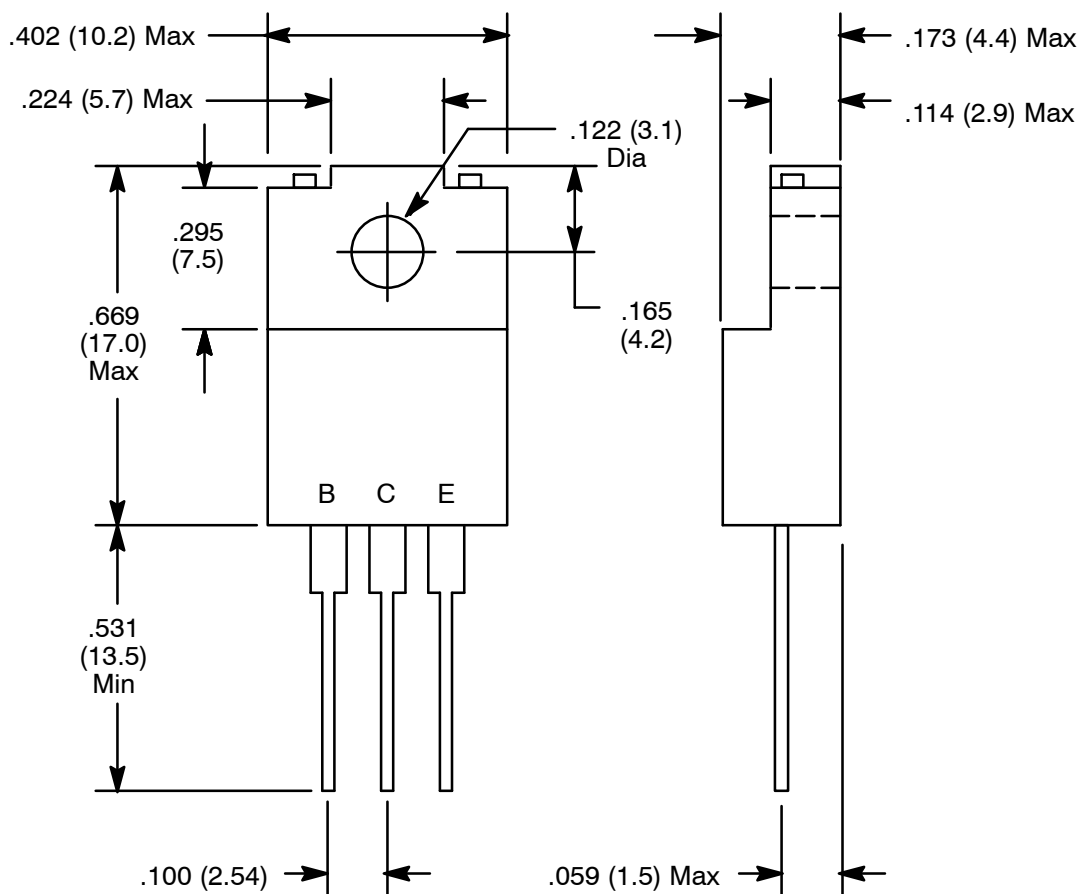
Note 1. Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 10\%$.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V, I_E = 0$	-	-	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	10	μA
DC Current Gain	$h_{FE} (1)$	$V_{CE} = 5V, I_C = 200\text{mA}$	20	-	40	
	$h_{FE} (2)$	$V_{CE} = 5V, I_C = 1A$	8	-	-	
Gain Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 200\text{mA}$	-	15	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, f = 1\text{MHz}$	-	60	-	pF
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5A, I_B = 300\text{mA}$	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1.5A, I_B = 300\text{mA}$	-	-	1.5	V

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}, I_E = 0$	1100	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 5\text{mA}, R_{BE} = \infty$	800	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}, I_C = 0$	7	-	-	V
Collector-Emitter Sustaining Voltage	$V_{CEX(sus)}$	$I_C = 1.5\text{A}, I_{B1} = I_{B2} = 300\text{mA}, L = 2\text{mH}, \text{Clamped}$	800	-	-	V
Turn-On Time	t_{on}	$V_{CC} = 400\text{V}, I_{B1} = -2.5\text{A}, I_{B2} = I_C = 2\text{A}, R_L = 200\Omega$	-	-	0.5	μs
Storage Time	t_{stg}		-	-	3.0	μs
Fall Time	t_f		-	-	0.3	μs



NOTE: Tab is isolated